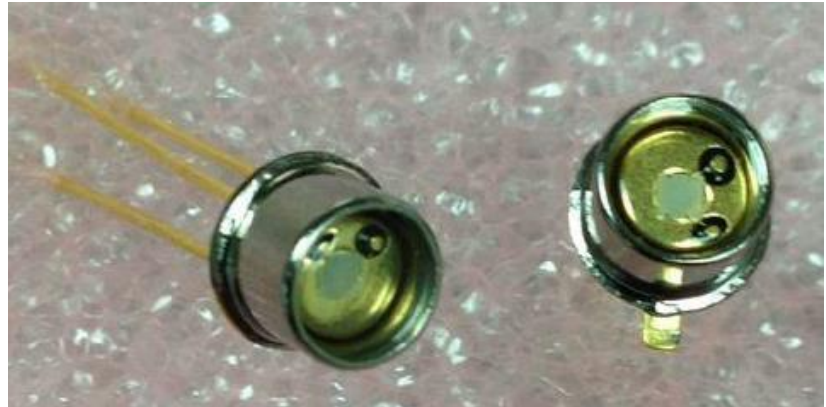


SiC Photodiode

UV0.25-3L

200nm–400...450nm
0,5mm x 0,5mm



Description

Broad band SiC based UV photodiode, it is optimized for ultra-violet, UVA, UVB and UVC wavelength. It can be easily selected with integral filters. It is packaged in electrically isolated and hermetically sealed TO-46 metal can with quartz window.

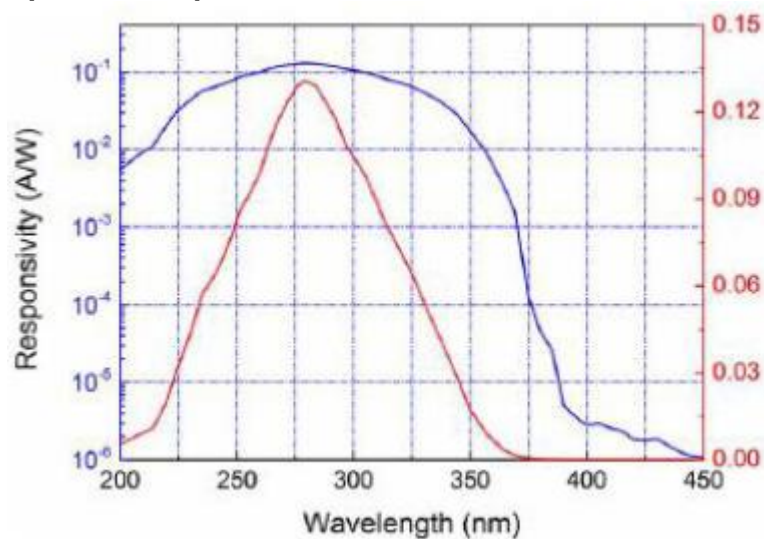
Features

- * High reliability in demanding environments
- * Photovoltaic mode operation
- * Good visible blindness

Applications

- * Sunlight exposure meter
- * UV power meter
- * Water purification facilities
- * flame detection

Spectral Response



OEC



Opto-Electronic
Components



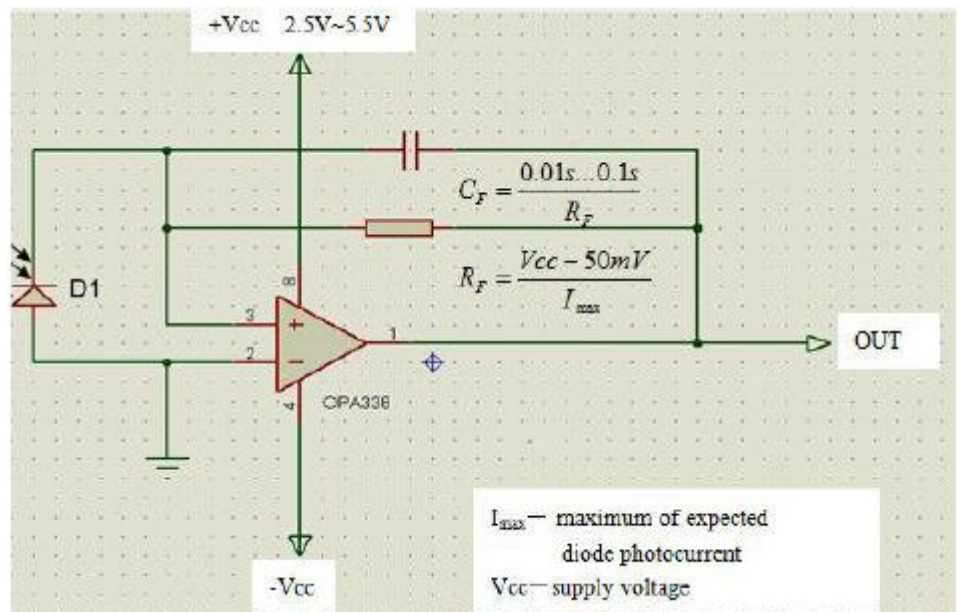
Electro-optical Parameters (@ 23°C +,- 2°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit
Operation temperature range	T _{opt}	-25		+120	°C
Storage temperature range	T _{sto}	-40		+120	°C
Soldering temperature (3s)	T _{sol}		260		°C
Reverse voltage	V _r		-20		V
Chip size (active area)	A		0.25		mm ²
Dark current (V _r =-5V)	I _d			0.1	nA
Temperature coefficient	T _c		-0.1		%/°C
Capacitance (V _r =0V, f=1MHz)	C _j		23		pF
Wavelength of peak responsivity	λ _p		280		nm
Peak responsivity (@280nm)	R _{max}		0.13		A/W
Spectral response range (R=0.1*R _{max})	S _R	215		360	nm
UV-Visible rejection ratio(R _{max} /R _{400nm})	-	10 ⁴			-

Tabular data for 0,5mm x 0,5mm active area

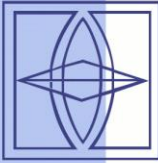
Rise & Fall Time within the range of 100 – 500µs
Maximum Power Load 1W / cm² (10mW / mm²)
Option active area with 1mm x 1mm (1mm²)

Typical Application Circuit



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Package

